Abstracts

A 240 W push-pull GaAs power FET for W-CDMA base stations

K. Inoue, K. Ebihara, H. Haematsu, T. Igarashi, H. Takahashi and J. Fukaya. "A 240 W push-pull GaAs power FET for W-CDMA base stations." 2000 MTT-S International Microwave Symposium Digest 00.3 (2000 Vol. III [MWSYM]): 1719-1722.

A 240 W power FET for cellular base stations of a next generation system has been developed. The FET consists of four 60 W chips, which were fabricated by using our high efficiency and low distortion device technique, combined in a push-pull configuration. The developed FET achieved 240 W (53.8 dBm) output power, 11.2 dB linear gain and 54% power-added efficiency at 2.14 GHz. This is the highest output power device using GaAs FET technology.

❑ Return to main document.